

<b>SANYO</b>	No. 3468	<b>2SK1465</b>
		N-Channel MOS Silicon FET

Very High-Speed Switching Applications

**Features**

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

**Absolute Maximum Ratings at Ta = 25°C**

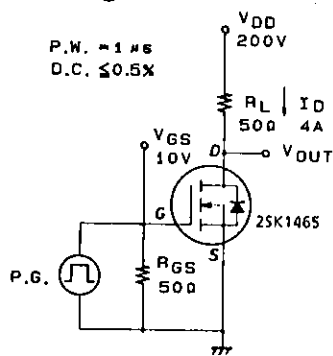
			unit
Drain to Source Voltage	V <sub>DSS</sub>	900	V
Gate to Source Voltage	V <sub>GSS</sub>	±30	V
Drain Current(DC)	I <sub>D</sub>	8	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	16 A
Allowable Power Dissipation	P <sub>D</sub>	Tc = 25°C	200 W
Channel Temperature	T <sub>ch</sub>		3.5 W
Storage Temperature	T <sub>stg</sub>		150 °C
			-55 to +150 °C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	900			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900V, V <sub>GS</sub> = 0			1.0	mA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	2.0		3.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> = 4A	2.5	5.0		S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 4A, V <sub>GS</sub> = 10V		1.2	1.6	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		1600		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		500		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		350		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 4A, V <sub>GS</sub> = 10V V <sub>DD</sub> = 200V, R <sub>GS</sub> = 50Ω		20		ns
Rise Time	t <sub>r</sub>		80		ns	
Turn-OFF Delay Time	t <sub>d(off)</sub>		350		ns	
Fall Time	t <sub>f</sub>		150		ns	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 8A, V <sub>GS</sub> = 0			1.8	V

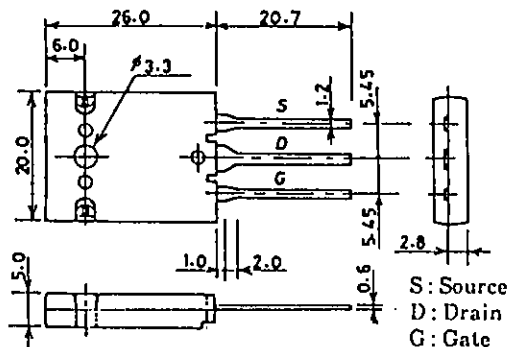
(Note) Be careful in handling the 2SK1465 because it has no protection diode between gate and source.

**Switching Time Test Circuit**



**Package Dimensions 2077**

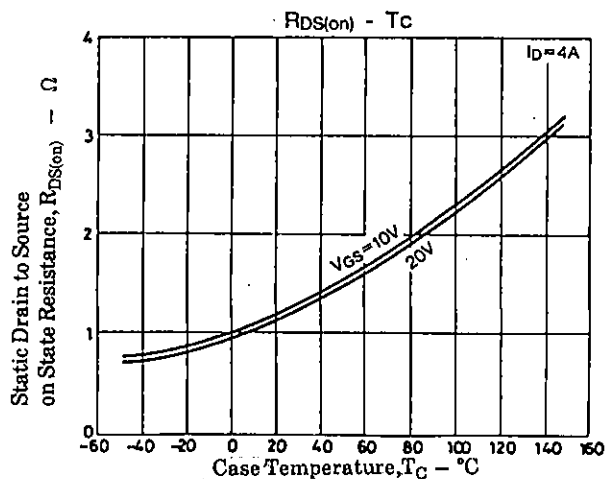
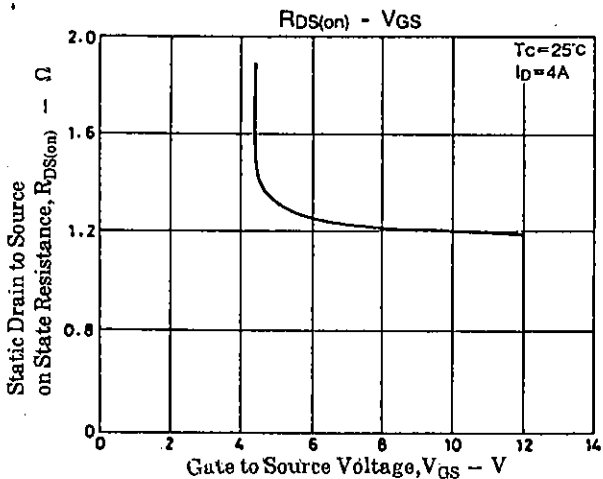
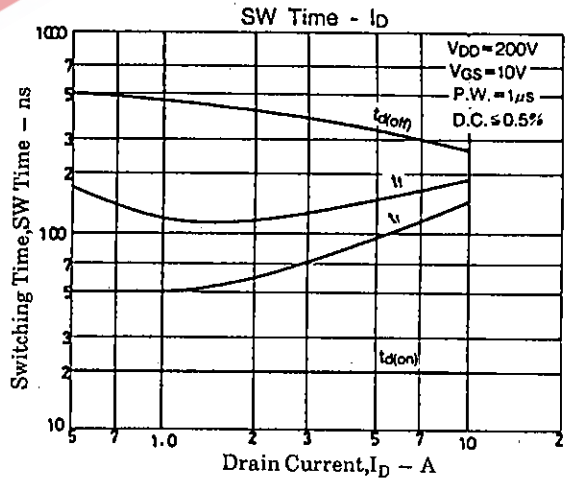
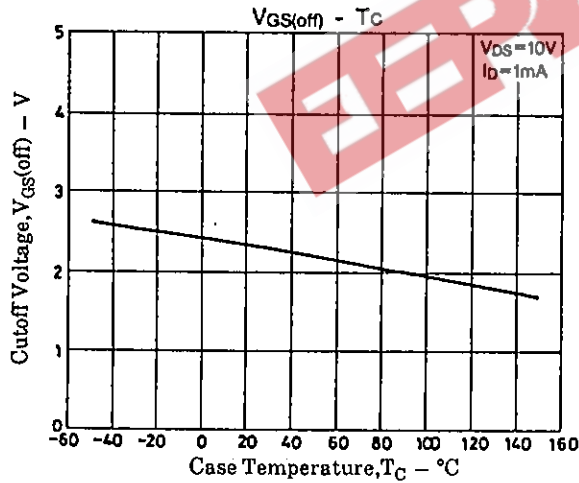
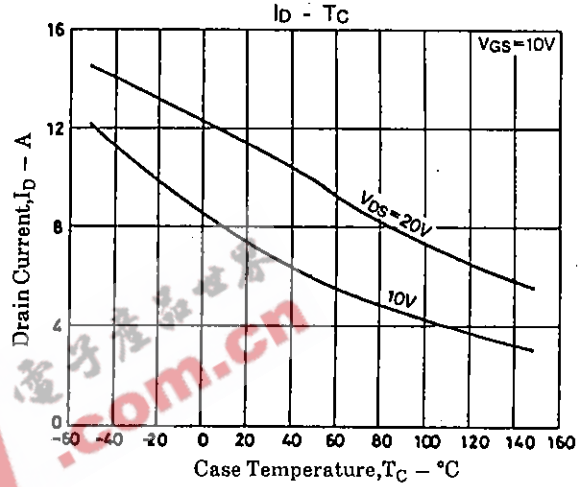
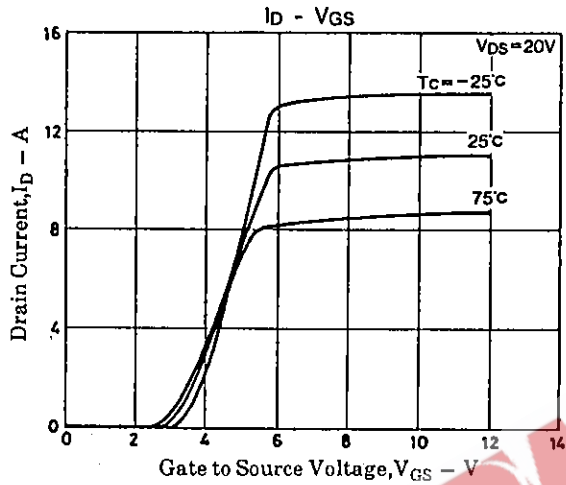
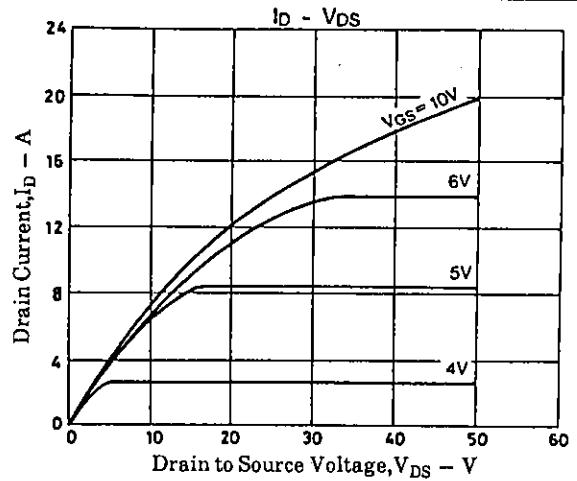
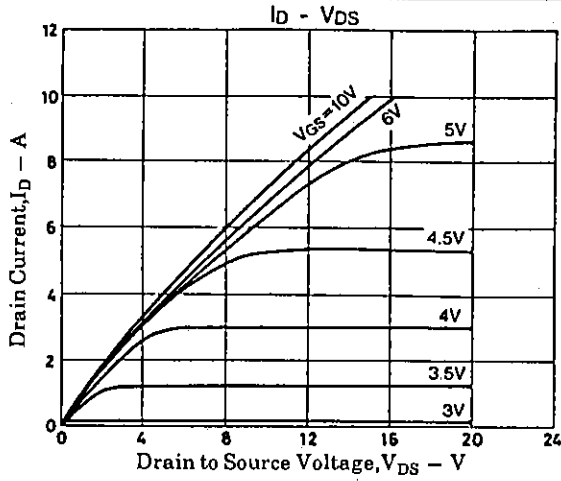
(unit: mm)

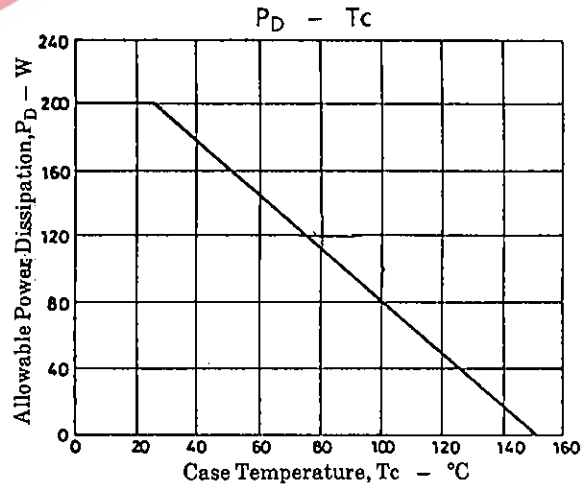
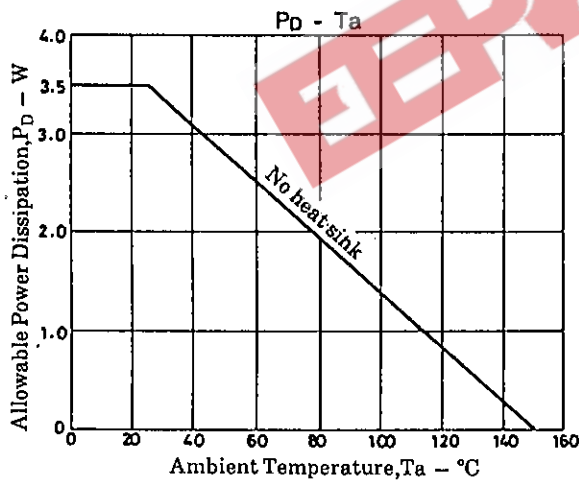
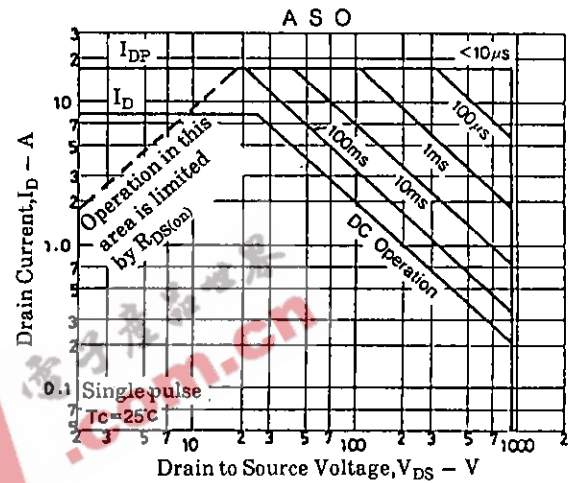
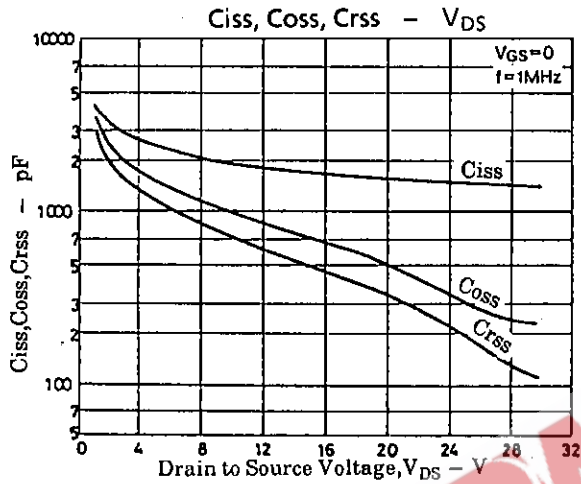
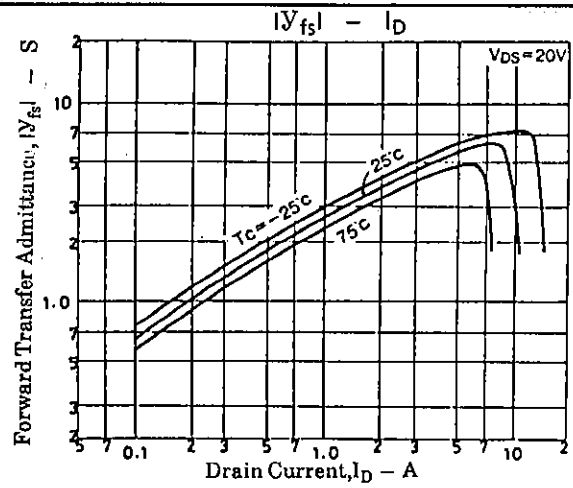
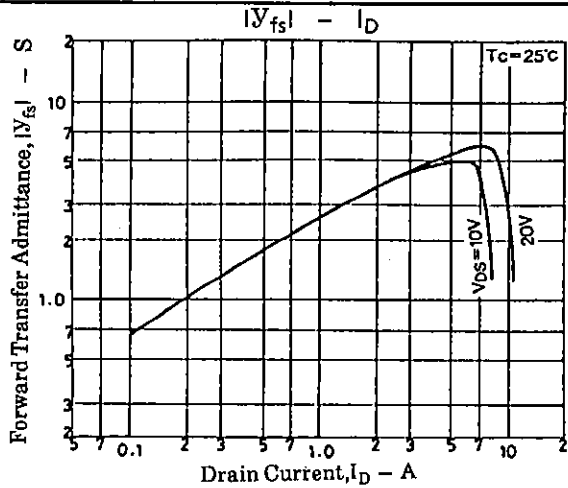


S: Source  
D: Drain  
G: Gate

SANYO: TO-3PBL

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